

**AMENDMENTS TO THE ABSTRACT**

Please substitute the following paragraph(s) for the abstract now appearing in the currently filed specification:

A substrate treatment ~~apparatus, comprising~~ apparatus includes a reaction tube (203) and a heater (207) heating a silicon ~~wafer (200)~~, wafer, wherein trimethyl Trimethyl aluminum (TMA) and ozone (O<sub>3</sub>) are alternately fed into the reaction tube ~~(203)~~ to generate Al<sub>2</sub>O<sub>3</sub> film on the surface of the wafer (200). The apparatus also ~~comprises~~ includes supply tubes ~~(232a) and (232b)~~ for flowing the ozone and TMA and a nozzle (233) supplying gas into the reaction tube (203). The two supply tubes ~~(232a) and (232b)~~ are connected to the nozzle (233) disposed inside the heater (207) in a zone inside the reaction tube (203) where a temperature is lower than a temperature near the ~~wafer (200)~~ wafer, and the ozone and TMA are supplied into the reaction tube (203) through the nozzle (233).